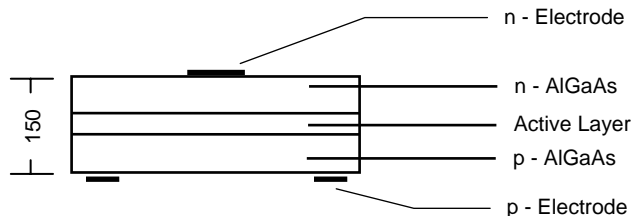
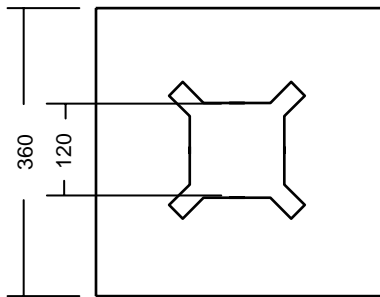


# TCS850



- ❖ Features:  
AlGaAs (DHS) / AlGaAs - substrate removed

- ❖ Outline Dimensions:



- ❖ Physical Structure:

Chip dimensions		Chip size	14 mil x 14 mil	360 $\mu\text{m}$ x 360 $\mu\text{m}$
		Thickness	5.9 mil	150 $\mu\text{m}$
		Bonding Pad	4.7 mil	120 $\mu\text{m}$
Electrode	Top	N (cathode)	Gold alloy	
	Backside	P (anode)	Gold alloy	

- ❖ Electro-Optical Characteristics:

Parameter	Symb ol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	$V_F$	$I_F = 20\text{mA}$	-	1.50	1.80	V
Reverse Current	$I_R$	$V_R = 5\text{V}$	-	-	10	$\mu\text{A}$
Peak Wavelength	$\lambda_P$	$I_F = 20\text{mA}$	-	850	-	nm
Output power	$P_O$	$I_F = 20\text{mA}$	2.5	3.4	-	mW